

# EXHIBIT 1



US007381657B2

(12) **United States Patent**  
**Zhang et al.**

(10) **Patent No.:** **US 7,381,657 B2**  
 (45) **Date of Patent:** **Jun. 3, 2008**

(54) **BIASED PULSE DC REACTIVE SPUTTERING OF OXIDE FILMS**  
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(\* ) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(21) Appl. No.: **10/954,182**

(Continued)

(22) Filed: **Oct. 1, 2004**

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(65) **Prior Publication Data**  
 US 2005/0048802 A1 Mar. 3, 2005

Li, Ning et al., "Enhancement of aluminum oxide physical vapor deposition with a secondary plasma", Nov. 28, 2001, Scien Direct, pp. 1-11.\*

(Continued)

**Related U.S. Application Data**

*Primary Examiner*—Michelle Estrada

(63) Continuation of application No. 10/101,863, filed on Mar. 16, 2002.

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(51) **Int. Cl.**  
*H01L 21/31* (2006.01)  
*H01L 21/469* (2006.01)  
 (52) **U.S. Cl.** ..... **438/769**; 438/770; 438/771; 257/E21.091; 257/E21.169; 257/E21.2; 257/E21.462; 257/E23.132

(57) **ABSTRACT**

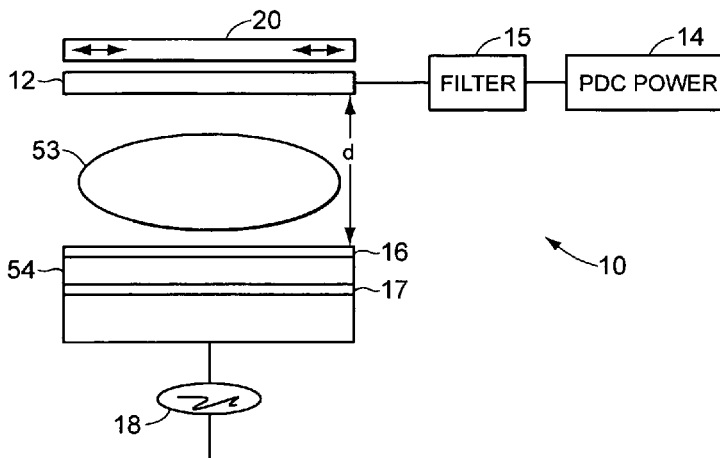
A biased pulse DC reactor for sputtering of oxide films is presented. The biased pulse DC reactor couples pulsed DC at a particular frequency to the target through a filter which filters out the effects of a bias power applied to the substrate, protecting the pulsed DC power supply. Films deposited utilizing the reactor have controllable material properties such as the index of refraction. Optical components such as waveguide amplifiers and multiplexers can be fabricated using processes performed on a reactor according to the present invention.

(58) **Field of Classification Search** ..... 438/769, 438/770, 771, 787, 788; 257/E23.132, E21.091, 257/E21.169, E21.2, E21.462  
 See application file for complete search history.

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**21 Claims, 27 Drawing Sheets**



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